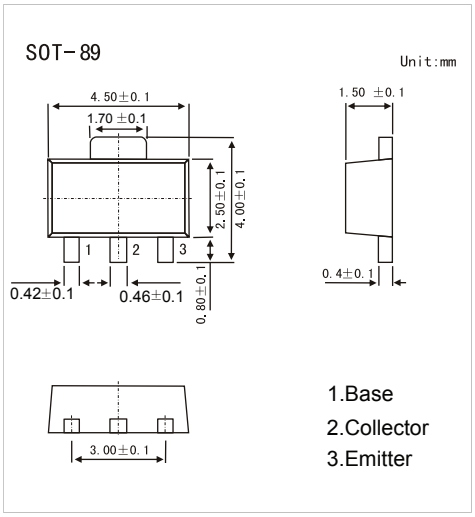
PNP Transistor

B772

■ Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882S



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current to Continuous	I_C	-3	A
Collector Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=-100uA ,I_E=0	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= -10 mA , I_B=0	-30			V
Emitter-base breakdown voltage	V_{EBO}	I_E= -100 uA ,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-40 V , I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V , I_C=0			-1	μA
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -1A	60		400	
		V_{CE}=-2V, I_C= -100mA	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A, I_B=- 0.2A			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-2A, I_B= -0.2A			-1.5	V
Transition frequency	f_T	V_{CE}=-5 V, I_C=-0.1mA,f = 10MHz	50			MHz

■ Classification of $h_{fe(1)}$

Type	2SB772S-R	2SB772S-Q	2SB772S-P	2SB772S-E
Range	60-120	100-200	160-320	200-400
Marking	772SR	772SQ	772SP	772SE

PNP Transistor

B772

■ Typical Characteristics

Fig.1 Static characteristics

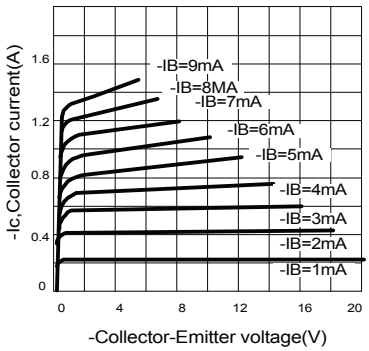


Fig.2 Derating curve of safe operating areas

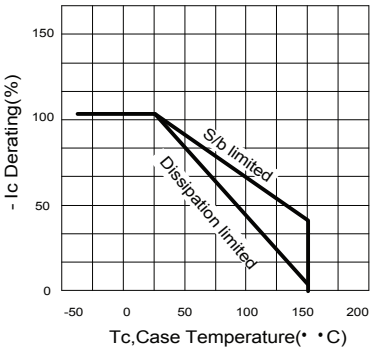


Fig.3 Power Derating

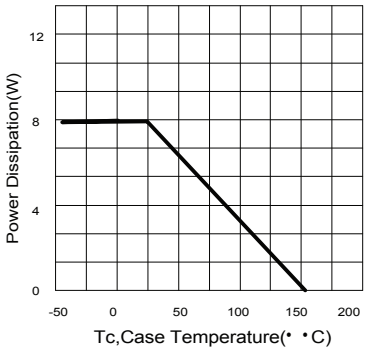


Fig.4 Collector Output capacitance

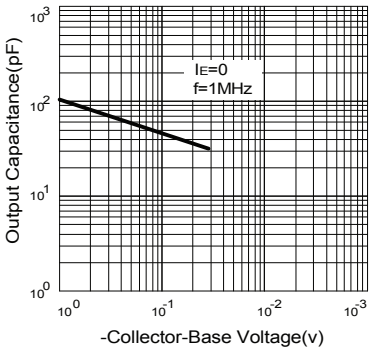


Fig.5 Current gain-bandwidth product

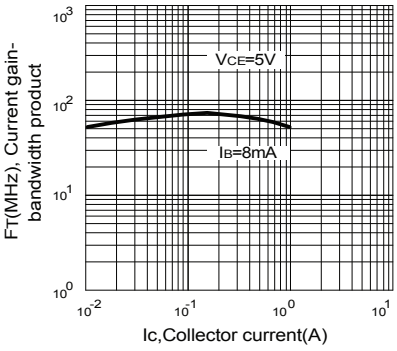


Fig.6 Safe operating area

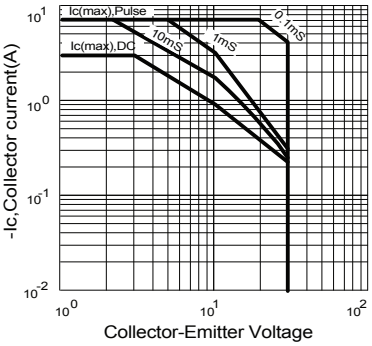


Fig.7 DC current gain

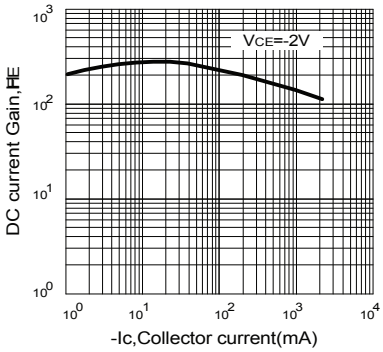


Fig.8 Saturation Voltage